

VRFA0006 - BD



WLAN 2.4GHz GaAs MMIC Dual Amplifier

Preliminary Datasheet v2

Features

- Frequency Range: 2.4-2.5 GHz / 5.15-5.85 GHz
- Integrated Dual Amplifier on a single die
- Single Supply Voltage
- Die Size: 3mm x 1mm x 0.1 mm



Description

The VRFA0030-BD The VRFA0006-BD is a single-chip solution for dual-band operation in WLAN applications. The MMIC operates at 2.4-2.5GHz, offering 26dB of gain and a 1dB compression point of 25dBm. In the 5.15-5.85GHz band, the device exhibits a small-signal gain of 28dB with a P1dB of 24dBm. The part can be readily integrated into a WIFI FEM fulfilling the EVM and ACP1-2 requirements for 802.11 a/b/g. The RF ports are DC blocked and matched to 50Ω.

Electrical Specifications

T=+25°C baseplate

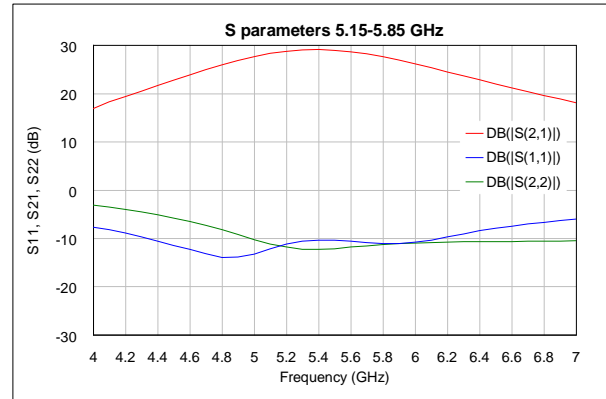
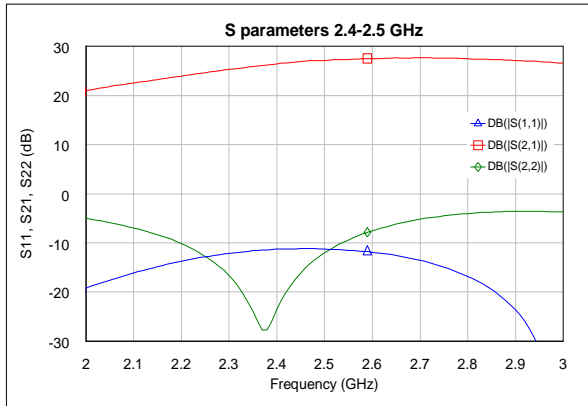
Parameter	Typical Specification		Unit
	2.4 GHz Amplifier	5 GHz Amplifier	
Frequency range	2.4-2.5	5.15-5.85	GHz
Gain	26.5	28	dB
Input Return Loss	-11	-10	dB
Output Return Loss	-12	-11	dB
Output power for 1dB compression	25	24	dBm
Drain supply	3-4.8	3-4.8	V
Gate supply	0.6-0.7	0.6-0.7	V
Drain current (class A)	200	160	mA

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Measured Performance (on wafer)

$T=+25^{\circ}\text{C}$ baseplate, $V_{DD} = +3.3\text{V}$, $I_d=300\text{mA}$



Recommended Absolute Maximum Ratings ^[1]

Parameter	Symbol	Value	Notes
Drain Bias Voltage	V_d	+10V	
Gate Bias Voltage	V_g	-5V	
Gate Current	I_g	5mA	
RF input power	RF_{in}	+5dBm	
Power Dissipation	P_d		Related to Junction Temperature
Junction Temperature	T_j	200°C	For maximum median device lifetime, T_j should be minimised
Storage Temperature	$T_{storage}$	-55 to 150°C	

^[1] Operation outside these conditions may cause permanent damage to the device. Combination of maximum rating conditions may reduce the values. Device performance at these ratings is not implied.

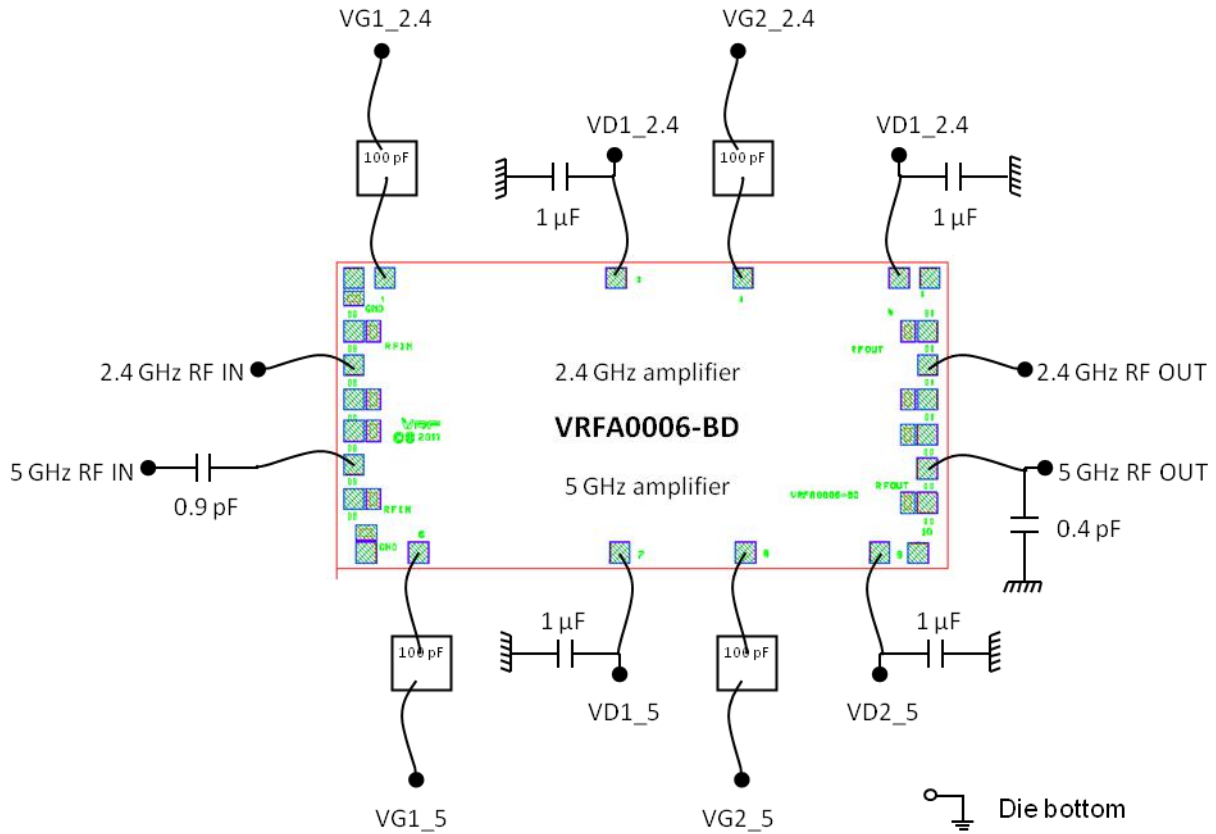
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Assembly & Bonding Diagram



Die Size	3mm x 1mm
Die Thickness	100μm
Minimum Bondpad opening	70μm x 70μm

Minimal length (0.15nH) are recommended for RF bondwires. The RF input and output ports are DC blocked.

GaAs devices are ESD sensitive and precautions should be observed during storage, handling, assembly and testing.

